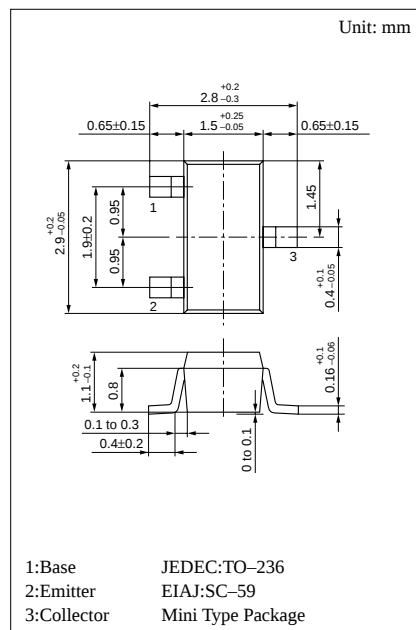


Silicon NPN epitaxial planer type

■ Features

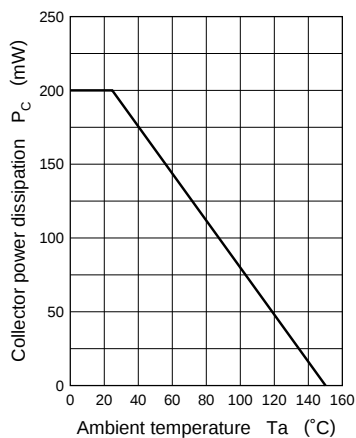
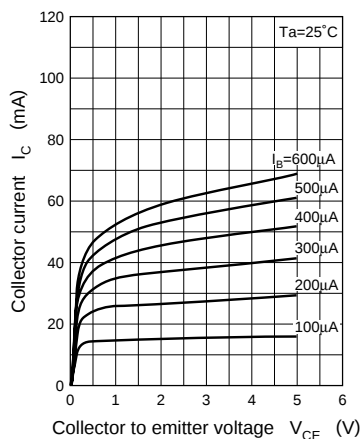
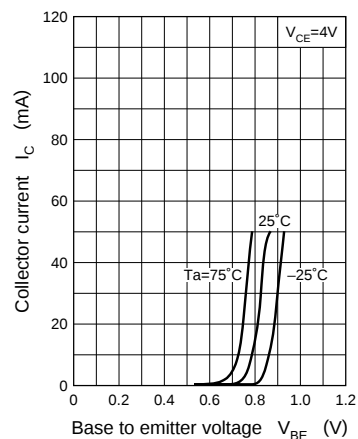
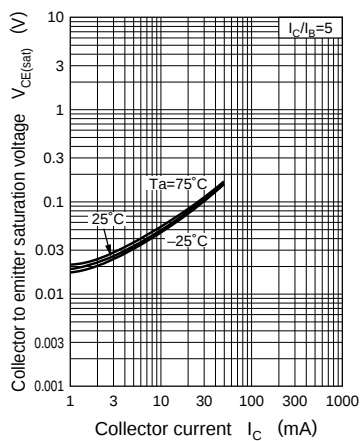
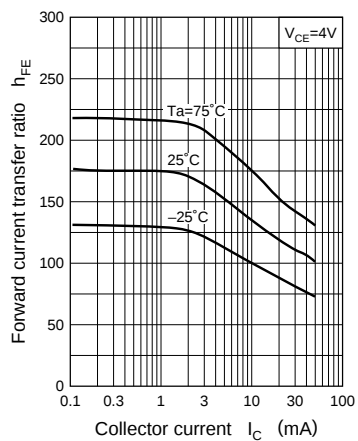
- High transition frequency f_T .
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	8	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^{\circ}\text{C}$
Storage temperature	T_{stg}	$-55 \sim +150$	$^{\circ}\text{C}$



Marking symbol : FB

Parameter	Symbol	Conditions	min	typ	max	Unit
Emitter cutoff current	I_{EBO}	$V_{EB} = 2V, I_C = 0$			2	μA
Collector to base voltage	V_{CBO}	$I_C = 100\mu A, I_E = 0$	15			V
Forward current transfer ratio	h_{FE}	$V_{CE} = 4V, I_C = 2mA$	100		350	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 20mA, I_B = 4mA$			0.5	V
Base to emitter voltage	V_{BE}	$V_{CE} = 4V, I_C = 2mA$		0.7		V
Transition frequency	f_T	$V_{CB} = 10V, I_E = -15mA, f = 200MHz$	0.8	1.3	1.9	GHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	0.6	1.0	1.4	pF
Common emitter reverse transfer capacitance	C_{rb}	$V_{CB} = 6V, I_E = 0, f = 1MHz$		0.4		pF
Power gain	PG	$V_{CB} = 10V, I_E = -10mA, f = 200MHz$	14	18	22	dB
h_{FE} ratio	$h_{FE(RATIO)}$	$V_{CE} = 4V, I_C = 100\mu A$	0.6		1.5	
		$V_{CE} = 4V, I_C = 2mA$				

$P_C - T_a$  $I_C - V_{CE}$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $C_{ob} - V_{CB}$ 